On the limitations of the definition of the intrinsic cut-off frequency from current gain equals to one

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***Abstract*—The intrinsic cut-off frequency (f_T) of nanoscale transistors based on the current gain equals to one (0 dB) is critically analyzed. Since f_T is a figure of merit when comparing different technologies, we suggest that predictions of f_T have to be based on numerical simulations of the delay time in the total (particle plus displacement) drain current. In some transistors, the values of f_T obtained from these time-dependent simulations can differ by nearly one order of magnitude from those obtained using (either quasi-static or non-quasi-static) expressions of the current gain.**

***Index Terms*—Cut-off frequency, displacement current, quasi-static approximation, nano transistor, time-dependent simulation.**

I. Introduction

THE definition of the intrinsic cut-off frequency (f_T) in field effect transistors (FETs) wants to quantify at which frequency the drain current stops correctly reproducing the gate voltage when all parasitic elements of the FET are not considered. Although f_T is usually not accessible experimentally (because parasitic elements are always there), its value is invoked as one of the most relevant parameter when comparing different technologies for future high-speed nano transistors [1].

In the literature [2]–[5], f_T is routinely estimated from Y-parameters by computing at which frequency the drain and gate currents become equal. The so-called quasi-static approximation of f_T is based on assuming that the drain current is only the DC component, while the gate current is the displacement component that grows linearly with frequency [6], [7]. Because of the total current conservation law, the gate displacement current is similar to the drain displacement one even at frequencies around f_T. Therefore, the quasi-static estimation, by its own construction, is not accurate enough and several non-quasi-static generalizations are developed [3]–[5].

In this letter, however, we argue that the estimation of f_T by fixing the current gain to one (0 dB) is ill-defined (with or without approximations). With such definition of f_T, it is possible to design FETs where the drain current, due to its own displacement component, becomes greater than the gate current at all frequencies, giving no value of f_T. However, the frequency where the FET stops working properly exists and it can be computed by recovering the basic definition of f_T based on the delay time of the drain current [8]. Although not discussed here, similar arguments could be invoked for the maximum oscillation frequency f_{max} when including input and output resistances.

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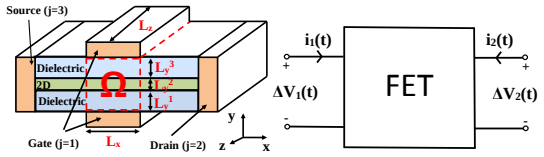

(a) (b)

Fig. 1. (a) Cross-section of active region $\Omega = L_x \times (L_y^1 + L_y^2 + L_y^3) \times L_z$ in a dual-gate 2D FET. (b) A two-port network of the intrinsic device.

II. Device structure and time-dependent simulation of the total currents

The results of this letter are based on analytical arguments and tested with accurate time-dependent numerical simulation of the currents in dual-gate FET with a 2D channel material with linear energy spectrum and energy gap[1]. The time-dependent currents are computed with the BITLLES simulator from self-consistent Monte Carlo solutions of the Boltzmann and Poisson equations with special attention to the displacement currents [9]–[11]. Our results only provide the intrinsic value of f_T because only active region Ω of the 2D FET plotted in Fig. 1(a) is simulated, without including the 3D-2D contact resistances (which is the well-known frequency bottleneck) or other parasitic elements [1]. The device A with volume $\Omega_A = 100 \times (45 + 1 + 45) \times 1125$ nm^3 will be considered.

We define the total (particle plus displacement) currents $i_j(t)$ where $j = 1, 2, 3$ correspond to gate, drain and source contacts, respectively, which satisfy the following total current conservation law:

$$i_1(t) + i_2(t) + i_3(t) = 0. \tag{1}$$

In Fig. 2 the transient currents in response to two square voltage pulses on the gate contact are indicated. For each contact j, we define the incremental charge:

$$\Delta Q_j \equiv \int_{t_0}^{t_\infty} (i_j(t) - i_j(t_\infty))\mathrm{d}t, \tag{2}$$

being t_0 the last time before the voltage increment, which corresponds to a steady-state value $i_j(t_0)$ in Fig. 2, and t_∞ the first time when the current gets a steady-state value $i_j(t_\infty)$ after the step voltage. Then, using (1) that ensures $i_1(t) +$

[1]The 2D material is inspired in graphene, but including a gap to avoid the unnecessary complications of Klein tunneling. For the same reason, the electron mean free path is considered larger than the simulation box.

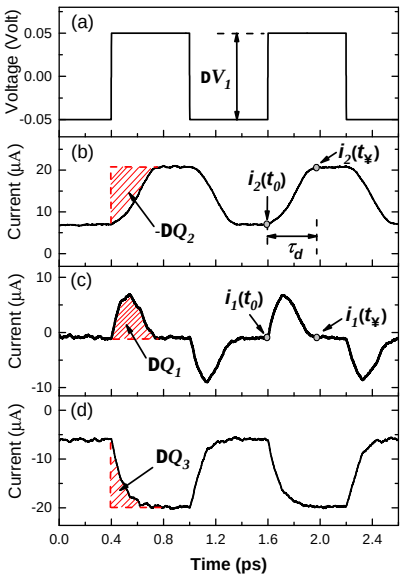

Fig. 2. Total (particle plus displacement) transient currents on the drain (b), gate (c) and source (d) contact of device A when a sequence of square voltage pulses (a) is applied on the gate contact.

$i_2(t) + i_3(t) - i_1(t_\infty) - i_2(t_\infty) - i_3(t_\infty) = 0$ at any time, we get:

$$\Delta Q_1 + \Delta Q_3 = -\Delta Q_2. \tag{3}$$

The incremental charges are illustrated in Fig. 2 (red dashed area) with $\Delta Q_1 = 11.62 \times 10^{-19}$ C, $\Delta Q_2 = -26.53 \times 10^{-19}$ C and $\Delta Q_3 = 14.91 \times 10^{-19}$ C. Notice that $\Delta Q_1 < |\Delta Q_2|$.

III. Definition of f_T from current gain

The usual definition of f_T comes from the two-port network model in Fig. 1(b). The frequency dependent component $Y_{mn}(\omega)$ of the admittance matrix due to a total current $i_m(t)$ collected on contact m when a perturbation ΔV_n is applied on contact n is given by [2]:

$$Y_{mn}(\omega) \equiv \frac{\Delta i_m}{\Delta V_n} + \frac{j\omega}{\Delta V_n} \int_{t_0}^{\infty} (i_m(t) - i_m(t_\infty))\, e^{-j\omega t} dt, \tag{4}$$

where ω is the angular frequency and $\Delta i_m = i_m(t_\infty) - i_m(t_0)$. Since we can consider in (4) that $i_m(t) - i_m(t_\infty) = 0$ for $t > t_\infty$, the current $i_m(t)$ correspond to the results of Fig. 2 from $t = t_0$ till $t = t_\infty$.

The intrinsic cut-off frequency f_T^{All} computed from the Y-parameters is the linear frequency at which the current gain magnitude drops to unity (0 dB) [2]:

$$|h_{21}(\omega = 2\pi f_T^{All})| \equiv |Y_{21}/Y_{11}| = 1. \tag{5}$$

The superindex All means that all orders of the Fourier transform in (4) are taken into account. We see in Fig. 3 (solid lines) that, for frequencies higher enough, $|Y_{21}^{All}|$ strongly depends on the frequency and $|Y_{11}^{All}|$ is no longer linear [12]. The value of $|Y_{21}^{All}|$ and $|Y_{11}^{All}|$ become equal at $f_T^{All} = 1.31$ THz.

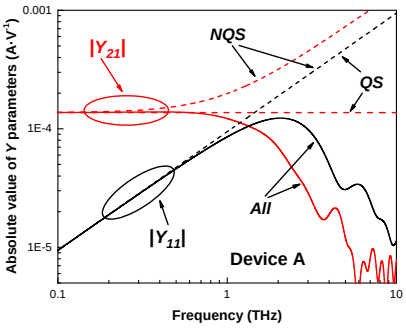

Fig. 3. Y parameters computed from the time-dependent simulation of the total (particle plus displacement) currents in device A using three different expressions. In solid lines, taken into account all orders (All) and in dashed lines with the non-quasi-static (NQS) or the quasi-static (QS) approximations.

A. Approximate estimations

A circuit representation of the high frequency behavior of nano transistors (instead of the physical time-dependent simulations of Fig. 2) is very welcome because it simplifies enormously the predictions of f_T. Since the exact behavior of the Fourier transform cannot be captured by simple circuits, approximations for (4) are invoked [3]–[5]. The standard expression for f_T is obtained under the so-called quasi-static approximation (QS). The term Y_{21} is computed without any frequency dependence, $e^{-j\omega t} \approx 0$, in (4):

$$Y_{21}^{QS}(\omega) = \frac{\Delta i_2}{\Delta V_1} = g_m, \tag{6}$$

where g_m is the transconductance. The term Y_{11} is computed with a zero order approximation, $e^{-j\omega t} \approx 1$, in (4):

$$Y_{11}^{QS}(\omega) = \frac{j\omega}{\Delta V_1} \int_0^{\infty} (i_1(t) - i_1(\infty))\, \mathrm{d}t = j\omega \frac{\Delta Q_1}{\Delta V_1}, \tag{7}$$

where ΔQ_1 from (2) is used. Then, from (5), we get the well-known expression:

$$f_T^{QS} = \frac{g_m}{2\pi \Delta Q_1/\Delta V_1} = \frac{g_m}{2\pi C}, \tag{8}$$

where the term $\Delta Q_1/\Delta V_1$ is associated to a capacitor C [12]. We get $f_T^{QS} = 1.45$ THz in Fig. 3 where the quasi-static approximation is accurate enough for low frequencies, but errors start to appear at frequencies well below f_T^{QS} because the drain displacement current cannot be neglected in (6), as indicated in the sum of currents in (1). Therefore, a zero order approximation of the drain current, $e^{-j\omega t} \approx 1$, in the computation of Y_{21} from (4) (as done for the gate current) could seem more appropriate:

$$\begin{aligned} Y_{21}^{NQS}(\omega) &= g_m + \frac{j\omega}{\Delta V_1} \int_0^{\infty} (i_2(t) - i_2(t_\infty))\, \mathrm{d}t \\ &= g_m - j\omega |\Delta Q_2|/\Delta V_1. \end{aligned} \tag{9}$$

Consequently, from (5), a non-quasi-static estimation (NQS) of f_T gives [13]:

$$f_T^{NQS} = \frac{g_m}{2\pi \sqrt{\Delta Q_1^2 - \Delta Q_2^2}/\Delta V_1}. \tag{10}$$

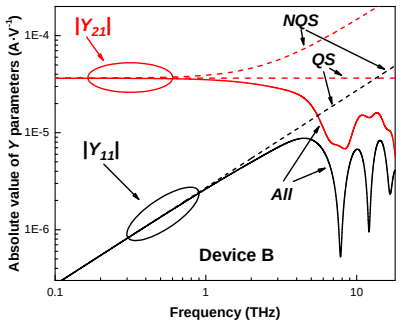

Fig. 4. Y parameters computed from time-dependent simulation of the total currents in device B using three different expressions (as in Fig. 3).

This definition of f_T^{NQS} is also problematic. According to (7) and (9), the terms ΔQ_1 and $|\Delta Q_2|$ control the frequency slope of $|Y_{11}^{QS}|$ and $|Y_{21}^{NQS}|$, respectively. Since $\Delta Q_1 < |\Delta Q_2|$ in (3), $|Y_{21}^{NQS}|$ and $|Y_{11}^{QS}|$ never cross as seen in Fig. 3.

The errors when neglecting the displacement current in the computation of f_T^{QS} can be quantified from (9). The elimination of the drain displacement current in front of the constant value g_m can be justified for frequencies where the later is larger or equal than the former, i.e. for frequencies lower than the critical frequency $f_c = g_m/(2\pi|\Delta Q_2|/\Delta V_1)$. However, since we have demonstrated in equation (3) that $|\Delta Q_2| > \Delta Q_1$, we always get $f_c < f_T^{QS}$ as can be seen in Fig. 3 with $f_c = 0.82$ THz $< f_T^{QS} = 1.45$ THz.

IV. The Definition of f_T from the Delay Time τ_d

Up to here, we have shown that the previous approximations of f_T are not always accurate. Here, we go a step further and show that the definition of f_T from Y-parameters in (5) is ill-defined. New FET designs with the condition $\Delta Q_1 \to 0$ will give a flattened Y_{11} and the condition $|h_{12}| = 1$ will be hardly achieved. We consider in Fig. 4 a different design (device B) with $\Omega_B = 20 \times (45+1+45) \times 200$ nm^3 implying smaller x and z dimensions. In the quasi-static estimation, because ΔQ_1 becomes smaller than that of device A, a higher $f_T^{QS} = 13.43$ THz is found. However, when f_T is computed without approximations, the condition $|h_{21}| = 1$ (0 dB) is never satisfied in the whole THz window, i.e. the $|Y_{21}^{All}|$ and $|Y_{11}^{All}|$ never cross in Fig. 4. Certainly, device B stops working properly at some frequency. In this letter, we suggest to recover the definition of the intrinsic cut-off frequency as $f_T \approx 1/(2\tau_d)$ being τ_d (plotted in Fig. 2) the minimum time that the drain current needs to reach its saturation value after the gate signals change [8]. In device A, we get $\tau_d = 0.352$ ps resulting $f_T = 1.42$ THz, which is similar to that of the quasi-static result. However, in device B, $\tau_d = 0.138$ ps (not plotted) giving $f_T = 3.62$ THz, which is very different from $f_T^{QS} = 13.43$ THz. It is important to emphasize that τ_d is not related to the electron transit time τ_e, but to the current delay time which explicitly depends on the displacement current. We can expect $\tau_d \approx \tau_e$ for a two-terminal ballistic device, while it is not true for three-terminal ones considered here [11], [14].

V. Conclusion

We show through analytical arguments supported by numerical simulations that the estimations of the intrinsic f_T based on $|h_{21}| = 1$ (with or without approximations) are questionable and definition of the intrinsic f_T based directly on the delay time τ_d obtained from time-dependent simulations of the currents is necessary. In spite of the difficulties in the experimental measurement of τ_d (in comparison with the accessibility of $|h_{21}(\omega)| = 1$ by extrapolating the results of S-parameters at lower frequencies), we conclude that definition of f_T from current gain equals to one can provide misleading results for nano transistors. The reasons why the problem raised in this letter has remained somehow unnoticed is, first, because the simple expression (8) captures the basic qualitative (not quantitative) behavior of f_T when nano transistors are scaled down (even in our results). Second, the explicit simulation of the time-dependent currents and τ_d demands huge amount of computational resources (specially for quantum simulations [10], [11] where new fundamental features are involved [14]).

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